TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

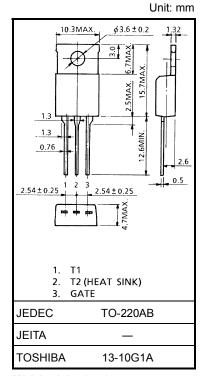
SM8G45, SM8J45, SM8G45A, SM8J45A

AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage: VDRM = 400V, 600V
- R.M.S On-State Current: IT (RMS) = 8A
- High Commutating (dv / dt)

MAXIMUM RATINGS

| CHARACTERI | STIC | SYMBOL | RATING | UNIT | |
|---|-------------------|----------------------|-----------|------------------|--|
| Repetitive Peak Off- | SM8G45 SM8G45A | V _{DRM} | 400 | ٧ | |
| State Voltage | SM8J45 SM8J45A | V DRM | 600 | | |
| R.M.S On-State Curren (Full Sine Waveform Tc | • | I _{T (RMS)} | 8 | А | |
| Peak One Cycle Surge | On-State | I _{TSM} | 80 (50Hz) | Α | |
| Current (Non-Repetitive | e) | | 88 (60Hz) | | |
| I ² t Limit Value | | I ² t | 32 | A ² s | |
| Critical Rate of Rise of C Current | On-State | di / dt | 50 | A / μs | |
| Peak Gate Power Dissip | ation | P _{GM} | 5 | W | |
| Average Gate Power Dis | ssipation | P _{G (AV)} | 0.5 | W | |
| Peak Gate Voltage | | V_{GM} | 10 | V | |
| Peak Gate Current | | I _{GM} | 2 | Α | |
| Junction Temperature | | Tj | -40~125 | °C | |
| Storage Temperature Ra | ange | T _{stg} | -40~125 | °C | |



Weight: 2.0 g (typ.)

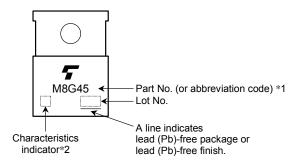


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

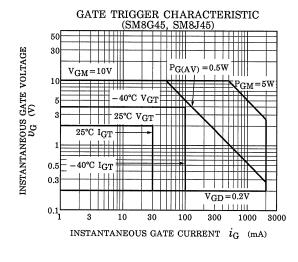
| CHARACTERISTIC | | SYMBOL | TEST CONDITION | | MIN | TYP. | MAX | UNIT | | |
|---|-----------|-----------------------|--|--|--|------------------|-----|------|----------|----|
| Repetitive Peak Current | Off-State | | | I _{DRM} | V _{DRM} = Rated, T _j = 125°C | | _ | _ | 2 | mA |
| Gate Trigger Voltage | | | I | | | T2 (+), Gate (+) | _ | _ | 2 | V |
| | SM8G4 | 5 | ; | | | T2 (+), Gate (-) | _ | _ | 2 | |
| | SM8J45 | 1 | III | | $V_D = 12V$ $R_L = 20\Omega$ | T2 (-), Gate (-) | _ | _ | 2 | |
| | | | IV | 1 ,, | | T2 (-), Gate (+) | _ | _ | _ | |
| | | | I | V _{GT} | | T2 (+), Gate (+) | _ | _ | 1.5 | |
| | SM8G4 | 5A | II | | | T2 (+), Gate (-) | _ | _ | 1.5 | |
| | SM8J45 | iΑ | III | | | T2 (-), Gate (-) | _ | _ | 1.5 | |
| | | | IV | | | T2 (-), Gate (+) | _ | _ | _ | |
| Gate Trigger Current | | | I | | V _D = 12V R _L = 20Ω | T2 (+), Gate (+) | _ | _ | 30 | mA |
| | SM8G4 | 5 | II | | | T2 (+), Gate (-) | _ | _ | 30 | |
| | SM8J45 | i | Ш | | | T2 (-), Gate (-) | _ | _ | 30 | |
| | | | IV | | | T2 (-), Gate (+) | _ | _ | _ | |
| | | | I | l _{GT} | | T2 (+), Gate (+) | _ | _ | 20 | |
| | SM8G4 | 5A | II | | | T2 (+), Gate (-) | _ | _ | 20 | |
| | SM8J45 | iΑ | III | | | T2 (-), Gate (-) | _ | _ | 20 | |
| | | | | | · | T2 (-), Gate (+) | _ | _ | _ |] |
| Peak On-State Voltage | | V_{TM} | I _{TM} = 12A | | _ | _ | 1.5 | V | | |
| Gate Non-Trigger Voltage | | V_{GD} | V _D = Rated, Tc = 125°C | | 0.2 | _ | _ | V | | |
| Holding Current | | lΗ | V _D = 12V, I _{TM} = 1A | | _ | _ | 50 | mA | | |
| Thermal Resistance | | R _{th (j-c)} | Junction to Case, AC | | _ | _ | 2.0 | °C/W | | |
| Critical Rate of SM8G45 Rise of Off-SM8J45 State Voltage at SM8G45A Commutation SM8J45A | | | (d) (dt) c | V_{DRM} = 400V, (di / dt) c = -4.5A / ms T_j = 125°C | | 10 | | | - V / μs | |
| | | | (dv / dt) c | | | 4 | | | | |

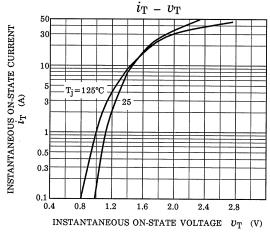
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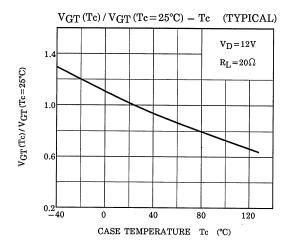
MARKING

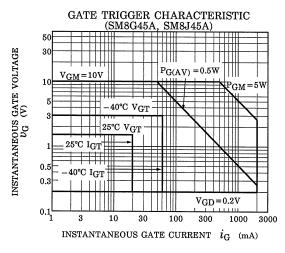


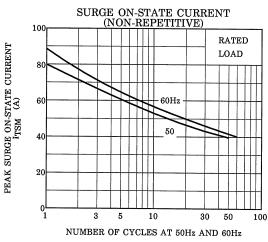
| | Part No. (or abbreviation code) | Part No. |
|----|------------------------------------|------------------|
| *1 | M8G45 | SM8G45, SM8G45A |
| | M8J45 | SM8J45, SM8J45A |
| *2 | Nothing | SM8G45, SM8J45 |
| | M8J45A | SM8G45A, SM8J45A |

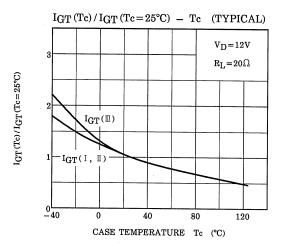


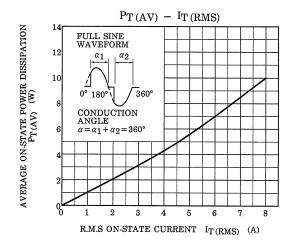


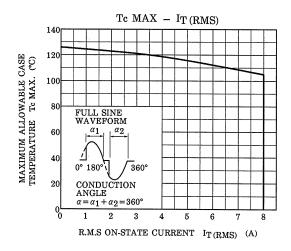


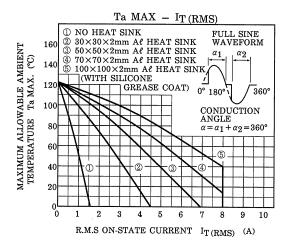


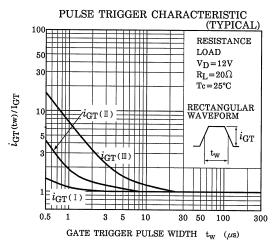


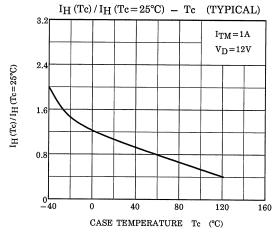


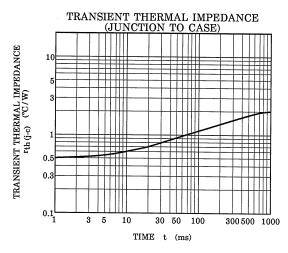












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